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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

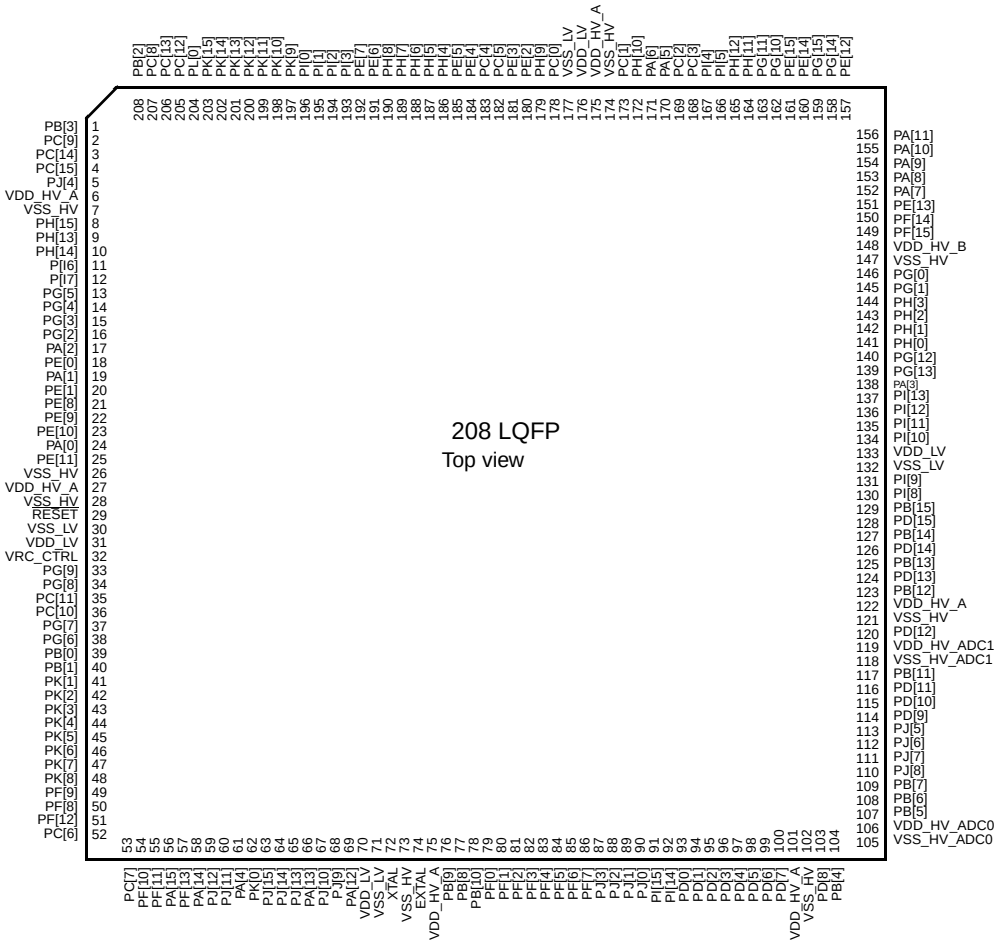
Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	e200z4d, e200z0h
Core Size	32-Bit Dual-Core
Speed	80MHz/120MHz
Connectivity	CANbus, Ethernet, I²C, LINbus, SCI, SPI
Peripherals	DMA, POR, PWM, WDT
Number of I/O	147
Program Memory Size	3MB (3M x 8)
Program Memory Type	FLASH
EEPROM Size	64K x 8
RAM Size	256K x 8
Voltage - Supply (Vcc/Vdd)	3V ~ 5.5V
Data Converters	A/D 27x10b, 5x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	176-LQFP
Supplier Device Package	176-LQFP (24x24)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/spc5646ccf0vlu1r

Table 1. MPC5646C family comparison[1] (continued)

Feature	MPC5644B		MPC5644C			MPC5645B		MPC5645C			MPC5646B		MPC5646C		
Package	176 LQFP	208 LQFP	176 LQFP	208 LQFP	256 BGA	176 LQFP	208 LQFP	176 LQFP	208 LQFP	256 BGA	176 LQFP	208 LQFP	176 LQFP	208 LQFP	256 BGA
Ethernet	No		Yes			No		Yes			No		Yes		
I^2C	1														
32 kHz oscillator (SXOSC)	Yes														
GPIO[12]	147	177	147	177	199	147	177	147	177	199	147	177	147	177	199
Debug	JTAG				Nexus 3+	JTAG				Nexus 3+	JTAG				Nexus 3+
Cryptographic Services Engine (CSE)	Optional														

NOTES:
1 Feature set dependent on selected peripheral multiplexing; table shows example.
2 Based on 125 °C ambient operating temperature and subject to full device characterisation.
3 The e200z0h can run at speeds up to 80 MHz. However, if system frequency is >80 MHz (e.g., e200z4d running at 120 MHz) the e200z0h needs to run at 1/2 system frequency. There is a configurable e200z0 system clock divider for this purpose.
4 DMAMUX also included that allows for software selection of 32 out of a possible 57 sources.
5 Not shared with 12-bit ADC, but possibly shared with other alternate functions.
6 There are 23 dedicated ANS plus 4 dedicated ANX channels on LQPF176. For higher pin count packages, there are 29 dedicated ANS plus 4 dedicated ANX channels.
7 16x precision channels (ANP) and 3x standard (ANS).
8 Not shared with 10-bit ADC, but possibly shared with other alternate functions.
9 As a minimum, all timer channels can function as PWM or Input Capture and Output Control. Refer to the eMIOS section of the device reference manual for information on the channel configuration and functions.
10 CAN Sampler also included that allows ID of CAN message to be captured when in low power mode.
11 STCU controls MBIST activation and reporting.
12 Estimated I/O count for proposed packages based on multiplexing with peripherals.



NOTE
1) VDD_HV_B supplies the IO voltage domain for the pins PE[12], PA[11], PA[10], PA[9], PA[8], PA[7], PE[13], PF[14], PF[15], PG[0], PG[1], PH[3], PH[2], PH[1], PH[0], PG[12], PG[13], and PA[3].
2) Availability of port pin alternate functions depends on product selection.

Figure 3. 208-pin LQFP configuration

	1	2	3	4	5	6	7	8	9	10	11	12	13	14	15	16	
A	PC[15]	PB[2]	PC[13]	PI[1]	PE[7]	PH[8]	PE[2]	PE[4]	PC[4]	PE[3]	PH[9]	PI[4]	PH[11]	PE[14]	PA[10]	PG[11]	A
B	PH[13]	PC[14]	PC[8]	PC[12]	PI[3]	PE[6]	PH[5]	PE[5]	PC[5]	PC[0]	PC[2]	PH[12]	PG[10]	PA[11]	PA[9]	PA[8]	B
C	PH[14]	VDD_HV_A	PC[9]	PL[0]	PI[0]	PH[7]	PH[6]	VSS_LV	VDD_HV_A	PA[5]	PC[3]	PE[15]	PG[14]	PE[12]	PA[7]	PE[13]	C
D	PG[5]	PI[6]	PJ[4]	PB[3]	PK[15]	PI[2]	PH[4]	VDD_LV	PC[1]	PH[10]	PA[6]	PI[5]	PG[15]	PF[14]	PF[15]	PH[2]	D
E	PG[3]	PI[7]	PH[15]	PG[2]	VDD_LV	VSS_LV	PK[10]	PK[9]	PM[1]	PM[0]	PL[15]	PL[14]	PG[0]	PG[1]	PH[0]	VDD_HV_A	E
F	PA[2]	PG[4]	PA[1]	PE[1]	PL[2]	PM[6]	PL[1]	PK[11]	PM[5]	PL[13]	PL[12]	PM[2]	PH[1]	PH[3]	PG[12]	PG[13]	F
G	PE[8]	PE[0]	PE[10]	PA[0]	PL[3]	VSS_HV	VSS_HV	VSS_HV	VSS_HV	VSS_HV	VSS_HV	PK[12]	VDD_HV_B	PI[13]	PI[12]	PA[3]	G
H	PE[9]	VDD_HV_A	PE[11]	PK[1]	PL[4]	VSS_LV	VSS_LV	VSS_HV	VSS_HV	VSS_HV	VSS_HV	PK[13]	VDD_HV_A	VDD_LV	VSS_LV	PI[11]	H
J	VSS_HV	VRC_CTRL	VDD_LV	PG[9]	PL[5]	VSS_LV	VSS_LV	VSS_LV	VSS_HV	VSS_HV	VSS_HV	PK[14]	PD[15]	PI[8]	PI[9]	PI[10]	J
K	RESET	VSS_LV	PG[8]	PC[11]	PL[6]	VSS_LV	VSS_LV	VSS_LV	VSS_LV	VDD_LV	VDD_LV	PM[3]	PD[14]	PD[13]	PB[14]	PB[15]	K
L	PC[10]	PG[7]	PB[0]	PK[2]	PL[7]	VSS_LV	VSS_LV	VSS_LV	VSS_LV	VDD_LV	VDD_LV	PM[4]	PD[12]	PB[12]	PB[13]	VDD_HV_ADC1	L
M	PG[6]	PB[1]	PK[4]	PF[9]	PK[5]	PK[6]	PK[7]	PK[8]	PL[8]	PL[9]	PL[10]	PL[11]	PB[11]	PD[10]	PD[11]	VSS_HV_ADC1	M
N	PK[3]	PF[8]	PC[6]	PC[7]	PJ[13]	VDD_HV_A	PB[10]	PF[6]	VDD_HV_A	PJ[1]	PD[2]	PJ[5]	PB[5]	PB[6]	PJ[6]	PD[9]	N
P	PF[12]	PF[10]	PF[13]	PA[14]	PJ[9]	PA[12]	PF[0]	PF[5]	PF[7]	PJ[3]	PI[15]	PD[4]	PD[7]	PD[8]	PJ[8]	PJ[7]	P
R	PF[11]	PA[15]	PJ[11]	PJ[15]	PA[13]	PF[2]	PF[3]	PF[4]	VDD_LV	PJ[2]	PJ[0]	PD[0]	PD[3]	PD[6]	VDD_HV_ADC0	PB[7]	R
T	PJ[12]	PA[4]	PK[0]	PJ[14]	PJ[10]	PF[1]	XTAL	EXTAL	VSS_LV	PB[9]	PB[8]	PI[14]	PD[1]	PD[5]	VSS_HV_ADC0	PB[4]	T
	1	2	3	4	5	6	7	8	9	10	11	12	13	14	15	16	

Notes:
1) VDD_HV_B supplies the IO voltage domain for the pins PE[12], PA[11], PA[10], PA[9], PA[8], PA[7], PE[13], PF[14], PF[15], PG[0], PG[1], PH[3], PH[2], PH[1], PH[0], PG[12], PG[13], PA[3], PM[3], and PM[4].
2)Availability of port pin alternate functions depends on product selection.

Figure 4. 256-pin BGA configuration

3.1 Pad types

In the device the following types of pads are available for system pins and functional port pins:

S = Slow[1]

M = Medium[1, 2]

1. See the I/O pad electrical characteristics in the device data sheet for details.
2. All medium and fast pads are in slow configuration by default at reset and can be configured as fast or medium. For example, Fast/Medium pad will be Medium by default at reset. Similarly, Slow/Medium pad will be Slow by default. Only exception is PC[1] which is in medium configuration by default (refer to PCR.SRC in the reference manual, Pad Configuration Registers (PCR0—PCR198)).

Table 4. Functional port pin descriptions (continued)

Port pin	PCR	Alternate function[1]	Function	Peripheral	I/O direction[2]	Pad type	RESET config.	Pin number		
								176 LQFP	208 LQFP	256 MAPBGA
PC[3]	PCR[35]	AF0 AF1 AF2 AF3 — — —	GPIO[35] CS0_1 MA[0] — CAN1RX CAN4RX EIRQ[6]	SIUL DSPI_1 ADC_0 — FlexCAN_1 FlexCAN_4 SIUL	I/O I/O O I I I	S	Tristate	144	168	C11
PC[4]	PCR[36]	AF0 AF1 AF2 AF3 ALT4 — — —	GPIO[36] E1UC[31] — FR_B_TX_EN SIN_1 CAN3RX EIRQ[18]	SIUL eMIOS_1 — Flexray DSPI_1 FlexCAN_3 SIUL	I/O I/O — O I I I	M/S	Tristate	159	183	A9
PC[5]	PCR[37]	AF0 AF1 AF2 AF3 ALT4 —	GPIO[37] SOUT_1 CAN3TX — FR_A_TX EIRQ[7]	SIUL DSPI_1 FlexCAN_3 — Flexray SIUL	I/O O O — O I	M/S	Tristate	158	182	B9
PC[6]	PCR[38]	AF0 AF1 AF2 AF3	GPIO[38] LIN1TX E1UC[28] —	SIUL LINFlexD_1 eMIOS_1 —	I/O O I/O —	S	Tristate	44	52	N3
PC[7]	PCR[39]	AF0 AF1 AF2 AF3 — —	GPIO[39] — E1UC[29] — LIN1RX WKPU[12]	SIUL — eMIOS_1 — LINFlexD_1 WKPU	I/O — I/O — I I	S	Tristate	45	53	N4
PC[8]	PCR[40]	AF0 AF1 AF2 AF3	GPIO[40] LIN2TX E0UC[3] —	SIUL LINFlexD_2 eMIOS_0 —	I/O O I/O —	S	Tristate	175	207	B3
PC[9]	PCR[41]	AF0 AF1 AF2 AF3 — —	GPIO[41] — E0UC[7] — LIN2RX WKPU[13]	SIUL — eMIOS_0 — LINFlexD_2 WKPU	I/O — I/O — I I	S	Tristate	2	2	C3

Table 4. Functional port pin descriptions (continued)

Port pin	PCR	Alternate function[1]	Function	Peripheral	I/O direction[2]	Pad type	RESET config.	Pin number		
								176 LQFP	208 LQFP	256 MAPBGA
PD[8]	PCR[56]	AF0 AF1 AF2 AF3 — —	GPI[56] — — — ADC0_P[12] ADC1_P[12]	SIUL — — — ADC_0 ADC_1	I — — — I I	I	Tristate	87	103	P14
PD[9]	PCR[57]	AF0 AF1 AF2 AF3 — —	GPI[57] — — — ADC0_P[13] ADC1_P[13]	SIUL — — — ADC_0 ADC_1	I — — — I I	I	Tristate	94	114	N16
PD[10]	PCR[58]	AF0 AF1 AF2 AF3 — —	GPI[58] — — — ADC0_P[14] ADC1_P[14]	SIUL — — — ADC_0 ADC_1	I — — — I I	I	Tristate	95	115	M14
PD[11]	PCR[59]	AF0 AF1 AF2 AF3 — —	GPI[59] — — — ADC0_P[15] ADC1_P[15]	SIUL — — — ADC_0 ADC_1	I — — — I I	I	Tristate	96	116	M15
PD[12]	PCR[60]	AF0 AF1 AF2 AF3 —	GPIO[60] CS5_0 E0UC[24] — ADC0_S[4]	SIUL DSPI_0 eMIOS_0 — ADC_0	I/O O I/O — I	S	Tristate	100	120	L13
PD[13]	PCR[61]	AF0 AF1 AF2 AF3 —	GPIO[61] CS0_1 E0UC[25] — ADC0_S[5]	SIUL DSPI_1 eMIOS_0 — ADC_0	I/O I/O I/O — I	S	Tristate	102	124	K14
PD[14]	PCR[62]	AF0 AF1 AF2 AF3 ALT4 —	GPIO[62] CS1_1 E0UC[26] — FR_DBG[0] ADC0_S[6]	SIUL DSPI_1 eMIOS_0 — Flexray ADC_0	I/O O I/O — O I	S	Tristate	104	126	K13

Table 4. Functional port pin descriptions (continued)

Port pin	PCR	Alternate function[1]	Function	Peripheral	I/O direction[2]	Pad type	RESET config.	Pin number		
								176 LQFP	208 LQFP	256 MAPBGA
PF[13]	PCR[93]	AF0 AF1 AF2 AF3 — —	GPIO[93] E1UC[26] — — LIN5RX WKPU[16]	SIUL eMIOS_1 — — LINFlexD_5 WKPU	I/O I/O — — I I	S	Tristate	49	57	P3
PF[14]	PCR[94]	AF0 AF1 AF2 AF3 ALT4	GPIO[94] CAN4TX E1UC[27] CAN1TX MDIO	SIUL FlexCAN_4 eMIOS_1 FlexCAN_1 FEC	I/O O I/O O I/O	M/S	Tristate	126	150	D14
PF[15]	PCR[95]	AF0 AF1 AF2 AF3 — — — —	GPIO[95] E1UC[4] — — RX_DV CAN1RX CAN4RX EIRQ[13]	SIUL eMIOS_1 — — FEC FlexCAN_1 FlexCAN_4 SIUL	I/O I/O — — I I I I	M/S	Tristate	125	149	D15
PG[0]	PCR[96]	AF0 AF1 AF2 AF3 ALT4	GPIO[96] CAN5TX E1UC[23] — MDC	SIUL FlexCAN_5 eMIOS_1 — FEC	I/O O I/O — O	F	Tristate	122	146	E13
PG[1]	PCR[97]	AF0 AF1 AF2 AF3 — — —	GPIO[97] — E1UC[24] — TX_CLK CAN5RX EIRQ[14]	SIUL — eMIOS_1 — FEC FlexCAN_5 SIUL	I/O — I/O — I I I	M	Tristate	121	145	E14
PG[2]	PCR[98]	AF0 AF1 AF2 AF3	GPIO[98] E1UC[11] SOUT_3 —	SIUL eMIOS_1 DSPI_3 —	I/O I/O O —	M/S	Tristate	16	16	E4
PG[3]	PCR[99]	AF0 AF1 AF2 AF3 —	GPIO[99] E1UC[12] CS0_3 — WKPU[17]	SIUL eMIOS_1 DSPI_3 — WKPU	I/O I/O I/O — I	S	Tristate	15	15	E1
PG[4]	PCR[100]	AF0 AF1 AF2 AF3	GPIO[100] E1UC[13] SCK_3 —	SIUL eMIOS_1 DSPI_3 —	I/O I/O I/O —	M/S	Tristate	14	14	F2

Table 4. Functional port pin descriptions (continued)

Port pin	PCR	Alternate function[1]	Function	Peripheral	I/O direction[2]	Pad type	RESET config.	Pin number		
								176 LQFP	208 LQFP	256 MAPBGA
PI[7]	PCR[135]	AF0 AF1 AF2 AF3 ALT4	GPIO[135] E1UC[31] CS1_4 CS1_5 CS1_6	SIUL eMIOS_1 DSPI_4 DSPI_5 DSPI_6	I/O I/O O O O	S	Tristate	12	12	E2
PI[8]	PCR[136]	AF0 AF1 AF2 AF3 —	GPIO[136] — — — ADC0_S[16]	SIUL — — — ADC_0	I/O — — — I	S	Tristate	108	130	J14
PI[9]	PCR[137]	AF0 AF1 AF2 AF3 —	GPIO[137] — — — ADC0_S[17]	SIUL — — — ADC_0	I/O — — — I	S	Tristate	—	131	J15
PI[10]	PCR[138]	AF0 AF1 AF2 AF3 —	GPIO[138] — — — ADC0_S[18]	SIUL — — — ADC_0	I/O — — — I	S	Tristate	—	134	J16
PI[11]	PCR[139]	AF0 AF1 AF2 AF3 — —	GPIO[139] — — — ADC0_S[19] SIN_3	SIUL — — — ADC_0 DSPI_3	I/O — — — I I	S	Tristate	111	135	H16
PI[12]	PCR[140]	AF0 AF1 AF2 AF3 —	GPIO[140] CS0_3 CS0_2 — ADC0_S[20]	SIUL DSPI_3 DSPI_2 — ADC_0	I/O I/O I/O — I	S	Tristate	112	136	G15
PI[13]	PCR[141]	AF0 AF1 AF2 AF3 —	GPIO[141] CS1_3 CS1_2 — ADC0_S[21]	SIUL DSPI_3 DSPI_2 — ADC_0	I/O O O — I	S	Tristate	113	137	G14
PI[14]	PCR[142]	AF0 AF1 AF2 AF3 — —	GPIO[142] — — — ADC0_S[22] SIN_4	SIUL — — — ADC_0 DSPI_4	I/O — — — I I	S	Tristate	76	92	T12

Table 8. Absolute maximum ratings (continued)

Symbol		Parameter	Conditions	Value		Unit
				Min	Max	
V_{RC_CTRL}[2]		Base control voltage for external BCP68 NPN device	Relative to V_{DD_LV}	0	V_{DD_LV} + 1	V
V_{SS_ADC}	SR	Voltage on VSS_HV_ADC0, VSS_HV_ADC1 (ADC reference) pin with respect to ground (V_{SS_HV})	—	V_{SS_HV} – 0.1	V_{SS_HV} + 0.1	V
$V_{DD\_HV\_ADC0}$	SR	Voltage on VDD_HV_ADC0 with respect to ground (V_{SS_HV})	—	–0.3	6.0	V
			Relative to $V_{DD\_HV\_A}$[3]	$V_{DD\_HV\_A}$ – 0.3	$V_{DD\_HV\_A}$+0.3	
$V_{DD\_HV\_ADC1}$[4]	SR	Voltage on VDD_HV_ADC1 with respect to ground (V_{SS_HV})	—	–0.3	6.0	V
			Relative to $V_{DD\_HV\_A}$[2]	$V_{DD\_HV\_A}$–0.3	$V_{DD\_HV\_A}$+0.3	
V_{IN}	SR	Voltage on any GPIO pin with respect to ground (V_{SS_HV})	Relative to $V_{DD\_HV\_A/HV\_B}$	$V_{DD\_HV\_A/HV\_B}$ –0.3	$V_{DD\_HV\_A/HV\_B}$ +0.3	V
I_{INJPAD}	SR	Injected input current on any pin during overload condition	—	–10	10	mA
I_{INJSUM}	SR	Absolute sum of all injected input currents during overload condition	—	–50	50	
I_{AVGSEG}[5]	SR	Sum of all the static I/O current within a supply segment ($V_{DD\_HV\_A}$ or $V_{DD\_HV\_B}$)	V_{DD} = 5.0 V ± 10%, PAD3V5V = 0		70	mA
			V_{DD} = 3.3 V ± 10%, PAD3V5V = 1		64	
$T_{STORAGE}$	SR	Storage temperature	—	–55[6]	150	°C

NOTES:
1. $V_{DD\_HV\_B}$ can be independently controlled from $V_{DD\_HV\_A}$. These can ramp up or ramp down in any order. Design is robust against any supply order.
2. This voltage is internally generated by the device and no external voltage should be supplied.
3. Both the relative and the fixed conditions must be met. For instance: If $V_{DD\_HV\_A}$ is 5.9 V, $V_{DD\_HV\_ADC0}$ maximum value is 6.0 V then, despite the relative condition, the max value is $V_{DD\_HV\_A}$ + 0.3 = 6.2 V.
4. PA3, PA7, PA10, PA11 and PE12 ADC_1 channels are coming from $V_{DD\_HV\_B}$ domain hence $V_{DD\_HV\_ADC1}$ should be within ±300 mV of $V_{DD\_HV\_B}$ when these channels are used for ADC_1.
5. Any temperature beyond 125 °C should limit the current to 50 mA (max).
6. This is the storage temperature for the flash memory.

Table 15. SLOW configuration output buffer electrical characteristics (continued)

Symbol		C	Parameter	Conditions[1,2]		Value			Unit
						Min	Typ	Max	
V_{OL}	CC	P	Output low level SLOW configuration	Push Pull	I_{OL} = 3 mA, V_{DD} = 5.0 V ± 10%, PAD3V5V = 0	—	—	$0.1V_{DD}$	V
		C			I_{OL} = 3 mA, V_{DD} = 5.0 V ± 10%, PAD3V5V = 1(3)	—	—	$0.1V_{DD}$	
		P			I_{OL} = 1.5 mA, V_{DD} = 3.3 V ± 10%, PAD3V5V = 1	—	—	0.5	

NOTES:
1 V_{DD} = 3.3 V ± 10% / 5.0 V ± 10%, T_A = –40 to 125 °C, unless otherwise specified.
2 V_{DD} as mentioned in the table is $V_{DD\_HV\_A}$/$V_{DD\_HV\_B}$.
3 The configuration PAD3V5 = 1 when V_{DD} = 5 V is only a transient configuration during power-up. All pads but RESET and Nexus output (MDOx, EVTO, MCKO) are configured in input or in high impedance state.

Table 16. MEDIUM configuration output buffer electrical characteristics

Symbol		C	Parameter	Conditions[1,2]		Value			Unit
						Min	Typ	Max	
V_{OH}	CC	C	Output high level MEDIUM configuration	Push Pull	I_{OH} = –3 mA, V_{DD} = 5.0 V ± 10%, PAD3V5V = 0	$0.8V_{DD}$	—	—	V
		C			I_{OH} = –1.5 mA, V_{DD} = 5.0 V ± 10%, PAD3V5V = 1[3]	$0.8V_{DD}$	—	—	
		C			I_{OH} = –2 mA, V_{DD} = 3.3 V ± 10%, PAD3V5V = 1	V_{DD} – 0.8	—	—	
V_{OL}	CC	C	Output low level MEDIUM configuration	Push Pull	I_{OL} = 3 mA, V_{DD} = 5.0 V ± 10%, PAD3V5V = 0	—	—	$0.2V_{DD}$	V
		C			I_{OL} = 1.5 mA, V_{DD} = 5.0 V ± 10%, PAD3V5V = 1(3)	—	—	$0.1V_{DD}$	
		C			I_{OL} = 2 mA, V_{DD} = 3.3 V ± 10%, PAD3V5V = 1	—	—	0.5	

NOTES:
1 V_{DD} = 3.3 V ± 10% / 5.0 V ± 10%, T_A = –40 to 125 °C, unless otherwise specified.
2 V_{DD} as mentioned in the table is $V_{DD\_HV\_A}$/$V_{DD\_HV\_B}$.
3 The configuration PAD3V5 = 1 when V_{DD} = 5 V is only a transient configuration during power-up. All pads but RESET and Nexus output (MDOx, EVTO, MCKO) are configured in input or in high impedance state.

ECC circuitry provides correction of single bit faults and is used to improve further automotive reliability results. Some units will experience single bit corrections throughout the life of the product with no impact to product reliability.

Table 28. Flash memory read access timing[1]

Symbol		C	Parameter	Conditions[2]		Frequency range	Unit
				Code flash memory	Data flash memory		
f_{READ}	CC	P	Maximum frequency for Flash reading	5 wait states	13 wait states	120 —100	MHz
		C		4 wait states	11 wait states	100—80	
		D		3 wait states	9 wait states	80—64	
		C		2 wait states	7 wait states	64—40	
		C		1 wait states	4 wait states	40—20	
		C		0 wait states	2 wait states	20—0	

NOTES:
1 Max speed is the maximum speed allowed including PLL frequency modulation (FM).
2 V_{DD} = 3.3 V ± 10% / 5.0 V ± 10%, T_A = –40 to 125 °C, unless otherwise specified.

4.10.2 Flash memory power supply DC characteristics

Table 29 shows the flash memory power supply DC characteristics on external supply.

Table 29. Flash memory power supply DC electrical characteristics

Symbol		Parameter	Conditions[1]		Value[2]			Unit
					Min	Typ	Max	
I_{CFREAD}[3]	CC	Sum of the current consumption on $V_{DD\_HV\_A}$ on read access	Flash memory module read f_{CPU} = 120 MHz + 2%[4]	Code flash memory			33	mA
I_{DFREAD}(3)				Data flash memory			13	
I_{CFMOD}(3)	CC	Sum of the current consumption on $V_{DD\_HV\_A}$ (program/erase)	Program/Erase on-going while reading flash memory registers f_{CPU} = 120 MHz + 2% (4)	Code flash memory			52	mA
I_{DFMOD}(3)				Data flash memory			13	
I_{CFLPW}(3)	CC	Sum of the current consumption on $V_{DD\_HV\_A}$ during flash memory low power mode		Code flash memory			1.1	mA
I_{CFPWD}(3)	CC	Sum of the current consumption on $V_{DD\_HV\_A}$ during flash memory power down mode		Code flash memory			150	µA
I_{DFPWD}(3)				Data flash memory			150	

NOTES:
1 V_{DD} = 3.3 V ± 10% / 5.0 V ± 10%, T_A = –40 to 125 °C, unless otherwise specified.
2 All values need to be confirmed during device validation.

To complete these trials, ESD stress can be applied directly on the device. When unexpected behavior is detected, the software can be hardened to prevent unrecoverable errors occurring.

4.11.2 Electromagnetic interference (EMI)

The product is monitored in terms of emission based on a typical application. This emission test conforms to the IEC61967-1 standard, which specifies the general conditions for EMI measurements.

Table 31. EMI radiated emission measurement[1,2]

Symbol		C	Parameter	Conditions		Value			Unit
						Min	Typ	Max	
—	SR	—	Scan range	—		0.150		1000	MHz
f_{CPU}	SR	—	Operating frequency	—		—	120	—	MHz
V_{DD_LV}	SR	—	LV operating voltages	—		—	1.28	—	V
S_{EMI}	CC	T	Peak level	V_{DD} = 5 V, T_A = 25 °C, LQFP176 package Test conforming to IEC 61967-2, f_{OSC} = 40 MHz/f_{CPU} = 120 MHz	No PLL frequency modulation	—	—	18	dBµV
					± 2% PLL frequency modulation	—	—	14[3]	dBµV

NOTES:
1. EMI testing and I/O port waveforms per IEC 61967-1, -2, -4.
2. For information on conducted emission and susceptibility measurement (norm IEC 61967-4), please contact your local marketing representative.
3. All values need to be confirmed during device validation.

4.11.3 Absolute maximum ratings (electrical sensitivity)

Based on two different tests (ESD and LU) using specific measurement methods, the product is stressed in order to determine its performance in terms of electrical sensitivity.

4.11.3.1 Electrostatic discharge (ESD)

Electrostatic discharges (a positive then a negative pulse separated by 1 second) are applied to the pins of each sample according to each pin combination. The sample size depends on the number of supply pins in the device (3 parts × (n+1) supply pin). This test conforms to the AEC-Q100-002/-003/-011 standard.

Table 32. ESD absolute maximum ratings[1,2]

Symbol	Ratings	Conditions	Class	Max value[3]	Unit
$V_{ESD(HBM)}$	Electrostatic discharge voltage (Human Body Model)	T_A = 25 °C conforming to AEC-Q100-002	H1C	2000	V
$V_{ESD(MM)}$	Electrostatic discharge voltage (Machine Model)	T_A = 25 °C conforming to AEC-Q100-003	M2	200	
$V_{ESD(CDM)}$	Electrostatic discharge voltage (Charged Device Model)	T_A = 25 °C conforming to AEC-Q100-011	C3A	500	
				750 (corners)	

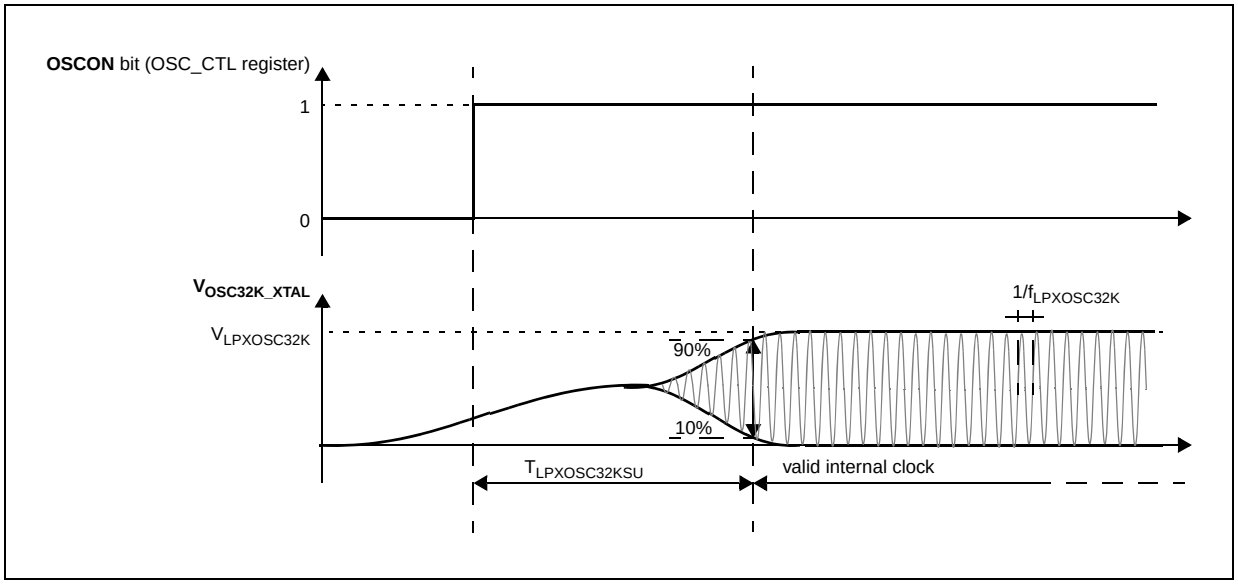


Figure 14. Slow external crystal oscillator (32 kHz) electrical characteristics

Table 37. Slow external crystal oscillator (32 kHz) electrical characteristics

Symbol		C	Parameter	Conditions[1]	Value[2]			Unit
					Min	Typ	Max	
f_{SXOSC}	SR	—	Slow external crystal oscillator frequency	—	32	32.768	40	kHz
g_{mSXOSC}	CC	—	Slow external crystal oscillator transconductance	V_{DD} = 3.3 V ± 10%,	13[3]	—	33[3]	µA/V
				V_{DD} = 5.0 V ± 10%	15[3]	—	35[3]	
V_{SXOSC}	CC	T	Oscillation amplitude	—	1.2	1.4	1.7	V
$I_{SXOSCBIAS}$	CC	T	Oscillation bias current	—	1.2	—	4.4	µA
I_{SXOSC}	CC	T	Slow external crystal oscillator consumption	—	—	—	7	µA
$T_{SXOSCSU}$	CC	T	Slow external crystal oscillator start-up time	—	—	—	2[4]	s

NOTES:
1 V_{DD} = 3.3 V ± 10% / 5.0 V ± 10%, T_A = –40 to 125 °C, unless otherwise specified.
2 All values need to be confirmed during device validation.
3 Based on ATE CZ
4 Start-up time has been measured with EPSON TOYOCOM MC306 crystal. Variation may be seen with other crystal.

4.14 FMPLL electrical characteristics

The device provides a frequency-modulated phase-locked loop (FMPLL) module to generate a fast system clock from the main oscillator driver.

Table 43. Conversion characteristics (12-bit ADC_1)

Symbol		C	Parameter	Conditions[1]	Value			Unit
					Min	Typ	Max	
V_{SS_ADC1}	SR	—	Voltage on VSS_HV_ADC1 (ADC_1 reference) pin with respect to ground (V_{SS_HV})[2]	—	–0.1		0.1	V
V_{DD_ADC1}[3]	SR	—	Voltage on VDD_HV_ADC1 pin (ADC_1 reference) with respect to ground (V_{SS_HV})	—	$V_{DD\_HV\_A}$ – 0.1		$V_{DD\_HV\_A}$ + 0.1	V
V_{AINx}[3,4]	SR	—	Analog input voltage[5]	—	V_{SS_ADC1} – 0.1		V_{DD_ADC1} + 0.1	V
f_{ADC1}	SR	—	ADC_1 analog frequency	—	8 + 2%		32 + 2%	MHz
t_{ADC1_PU}	SR	—	ADC_1 power up delay	—	1.5			µs
t_{ADC1_S}	CC	T	Sample time[6] VDD=5.0 V	—	440			ns
			Sample time(6) VDD=3.3 V	—	530			
t_{ADC1_C}	CC	P	Conversion time[7, 8] VDD=5.0 V	f_{ADC1} = 32 MHz	2			µs
			Conversion time(7), (6) VDD =5.0 V	$f_{ADC\ 1}$= 30 MHz	2.1			
			Conversion time(7), (6) VDD=3.3 V	$f_{ADC\ 1}$= 20 MHz	3			
			Conversion time(7), (6) VDD =3.3 V	f_{ADC1} = 15 MHz	3.01			
C_S	CC	D	ADC_1 input sampling capacitance	—	5			pF
C_{P1}	CC	D	ADC_1 input pin capacitance 1	—	3			pF
C_{P2}	CC	D	ADC_1 input pin capacitance 2	—	1			pF
C_{P3}	CC	D	ADC_1 input pin capacitance 3	—	1.5			pF
R_{SW1}	CC	D	Internal resistance of analog source	—			1	kΩ

7 Conversion time = Bit evaluation time + Sampling time + 1 Clock cycle delay.

8 Refer to ADC conversion table for detailed calculations.

9 Total Unadjusted Error: The maximum error that occurs without adjusting Offset and Gain errors. This error is a combination of Offset, Gain and Integral Linearity errors.

4.18 Fast Ethernet Controller

MII signals use CMOS signal levels compatible with devices operating at 3.3 V. Signals are not TTL compatible. They follow the CMOS electrical characteristics.

4.18.1 MII Receive Signal Timing (RXD[3:0], RX_DV, RX_ER, and RX_CLK)

The receiver functions correctly up to a RX_CLK maximum frequency of 25 MHz +1%. There is no minimum frequency requirement. In addition, the system clock frequency must exceed four times the RX_CLK frequency in 2:1 mode and two times the RX_CLK frequency in 1:1 mode.

Table 44. MII Receive Signal Timing

Spec	Characteristic	Min	Max	Unit
M1	RXD[3:0], RX_DV, RX_ER to RX_CLK setup	5	—	ns
M2	RX_CLK to RXD[3:0], RX_DV, RX_ER hold	5	—	ns
M3	RX_CLK pulse width high	35%	65%	RX_CLK period
M4	RX_CLK pulse width low	35%	65%	RX_CLK period

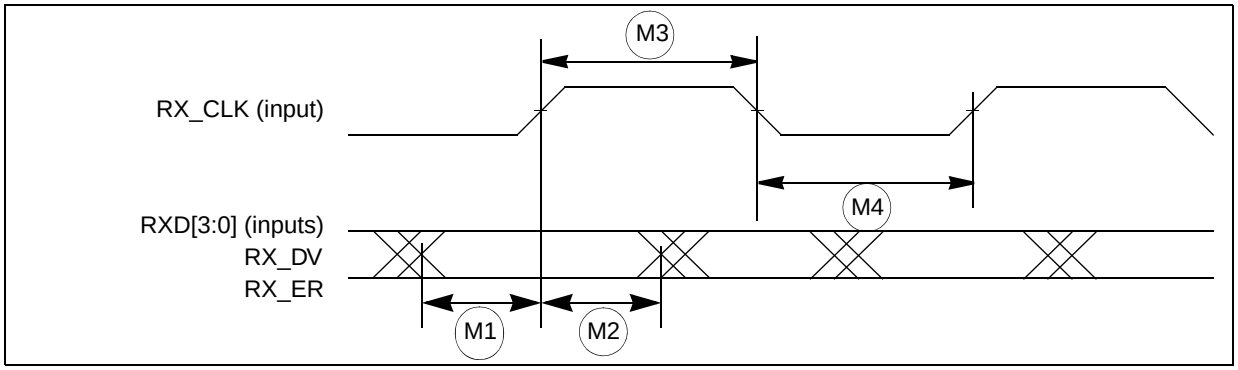


Figure 21. MII receive signal timing diagram

4.18.2 MII Transmit Signal Timing (TXD[3:0], TX_EN, TX_ER, TX_CLK)

The transmitter functions correctly up to a TX_CLK maximum frequency of 25 MHz +1%. There is no minimum frequency requirement. In addition, the system clock frequency must exceed four times the TX_CLK frequency in 2:1 mode and two times the TX_CLK frequency in 1:1 mode.

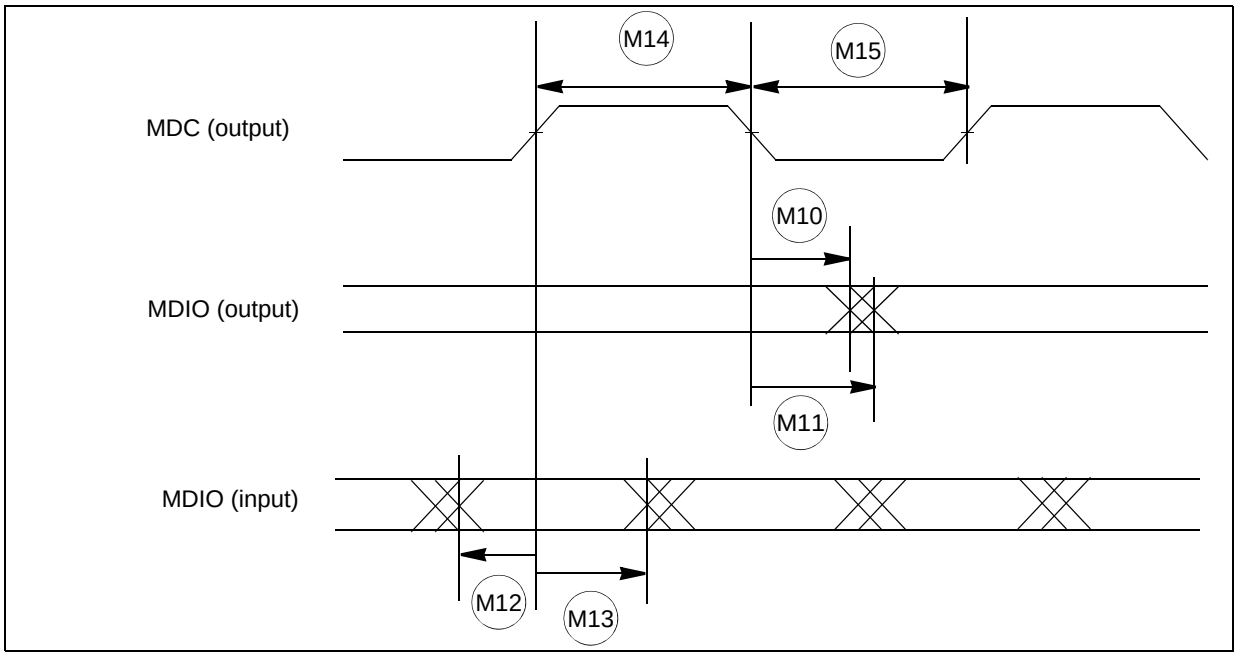


Figure 24. MII serial management channel timing diagram

4.19 On-chip peripherals

4.19.1 Current consumption

Table 48. On-chip peripherals current consumption[1]

Symbol		C	Parameter	Conditions		Value[2] Typ	Unit
$I_{DD\_HV\_A(CAN)}$	CC	D	CAN (FlexCAN) supply current on $V_{DD\_HV\_A}$	500 Kbps	Total (static + dynamic) consumption: FlexCAN in loop-back mode XTAL@8 MHz used as CAN engine clock source Message sending period is 580 µs	$7.652 \times f_{periph} + 84.73$	µA
				125 Kbps		$8.0743 \times f_{periph} + 26.757$	
$I_{DD\_HV\_A(eMIOS)}$	CC	D	eMIOS supply current on $V_{DD\_HV\_A}$	Static consumption: eMIOS channel OFF Global prescaler enabled		$28.7 \times f_{periph}$	
				Dynamic consumption: It does not change varying the frequency (0.003 mA)		3	
$I_{DD\_HV\_A(SCI)}$	CC	D	SCI (LINFlex) supply current on $V_{DD\_HV\_A}$	Total (static + dynamic) consumption: LIN mode Baudrate: 20 Kbps		$4.7804 \times f_{periph} + 30.946$	
$I_{DD\_HV\_A(SPI)}$	CC	D	SPI (DSPI) supply current on $V_{DD\_HV\_A}$	Ballast static consumption (only clocked)		1	
				Ballast dynamic consumption (continuous communication): Baudrate: 2 Mbit Transmission every 8 µs Frame: 16 bits		$16.3 \times f_{periph}$	
$I_{DD\_HV\_A(ADC)}$	CC	D	ADC supply current on $V_{DD\_HV\_A}$	V_{DD} = 5.5 V	Ballast static consumption (no conversion)	$0.0409 \times f_{periph}$	mA
				V_{DD} = 5.5 V	Ballast dynamic consumption (continuous conversion)	$0.0049 \times f_{periph}$	
IDD_HV_ADC0	CC	D	ADC_0 supply current on $V_{DD\_HV\_ADC0}$	V_{DD} = 5.5 V	Analog static consumption (no conversion)	200	µA
					Analog dynamic consumption (continuous conversion)	4	mA

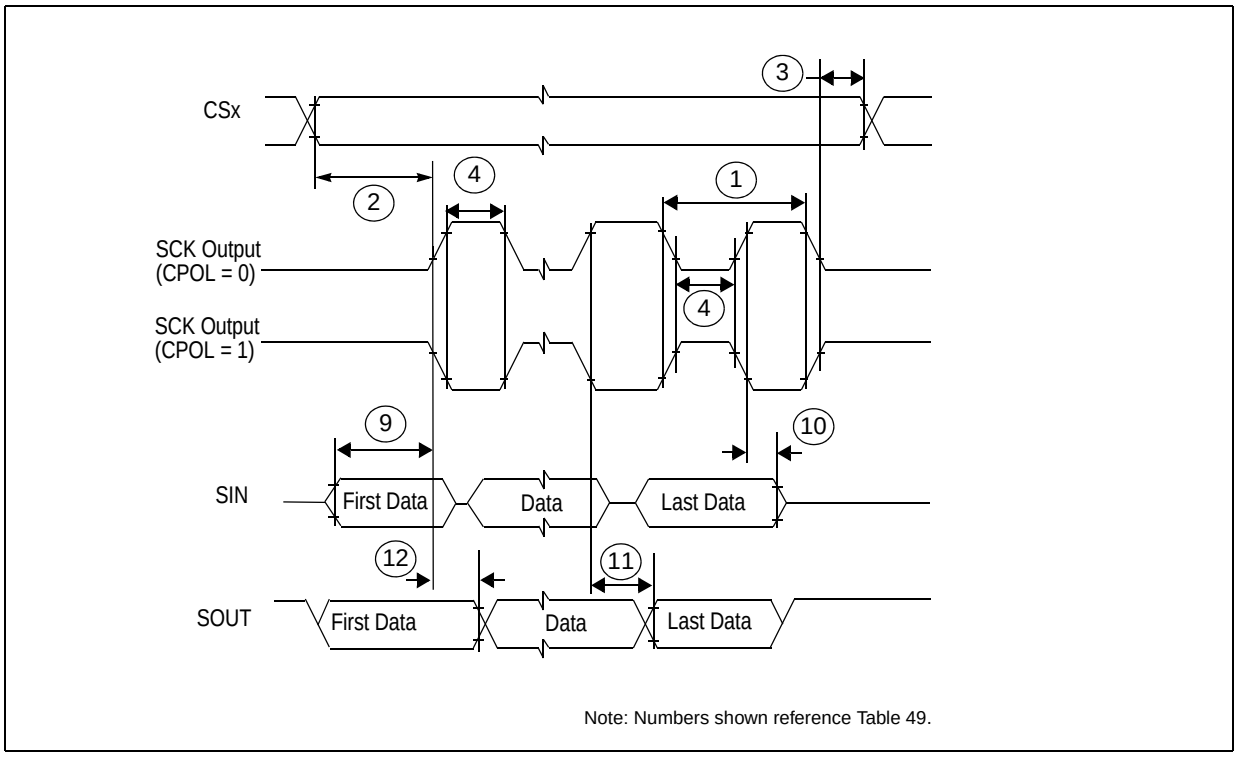


Figure 29. DSPI modified transfer format timing–master, CPHA = 0

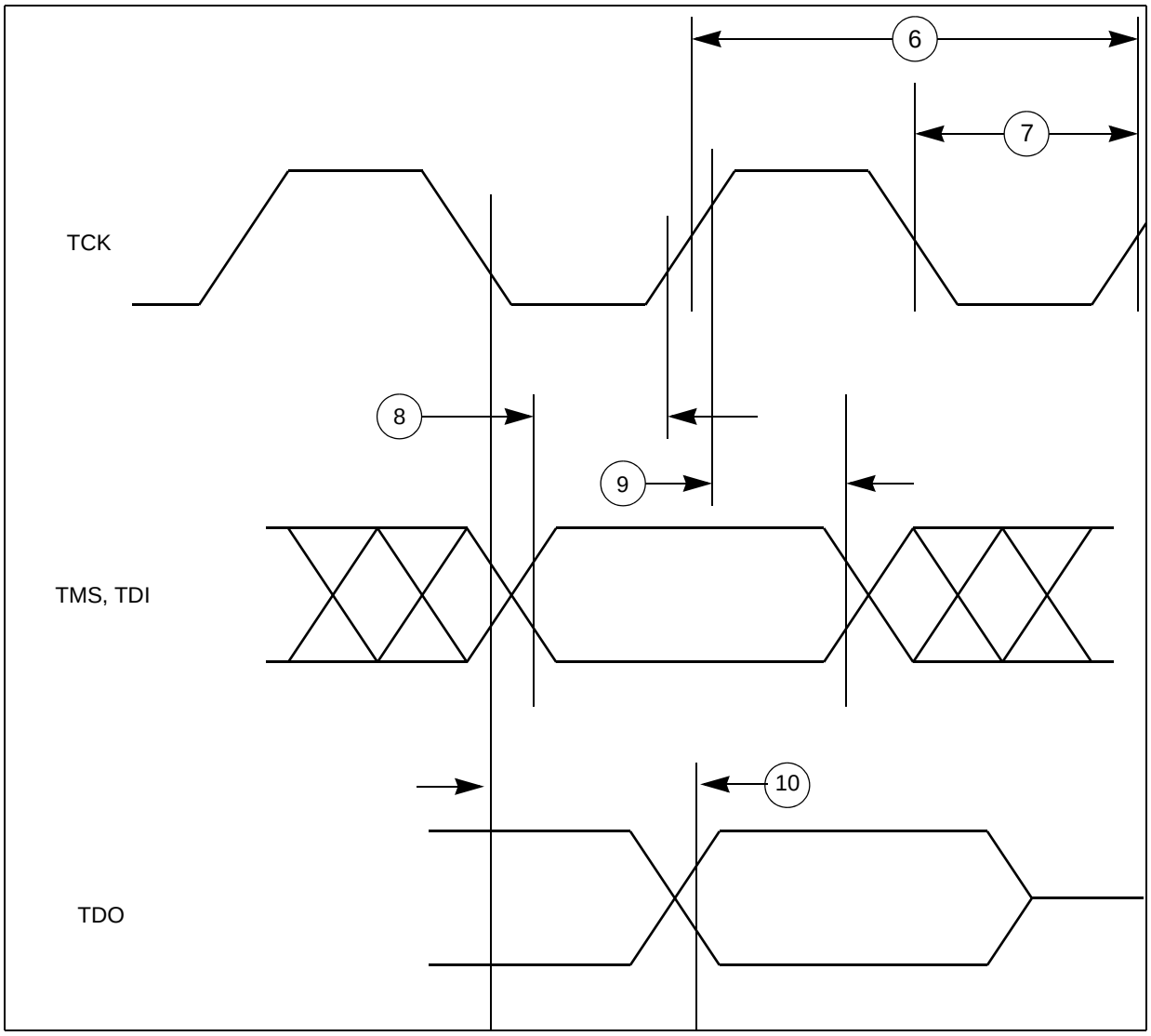


Figure 35. Nexus TDI, TMS, TDO timing

4.19.4 JTAG characteristics

Table 51. JTAG characteristics

No.	Symbol		C	Parameter	Value			Unit
					Min	Typ	Max	
1	t_{JCYC}	CC	D	TCK cycle time	64	—	—	ns
2	t_{TDIS}	CC	D	TDI setup time	10	—	—	ns
3	t_{TDIH}	CC	D	TDI hold time	5	—	—	ns
4	t_{TMSS}	CC	D	TMS setup time	10	—	—	ns
5	t_{TMSH}	CC	D	TMS hold time	5	—	—	ns

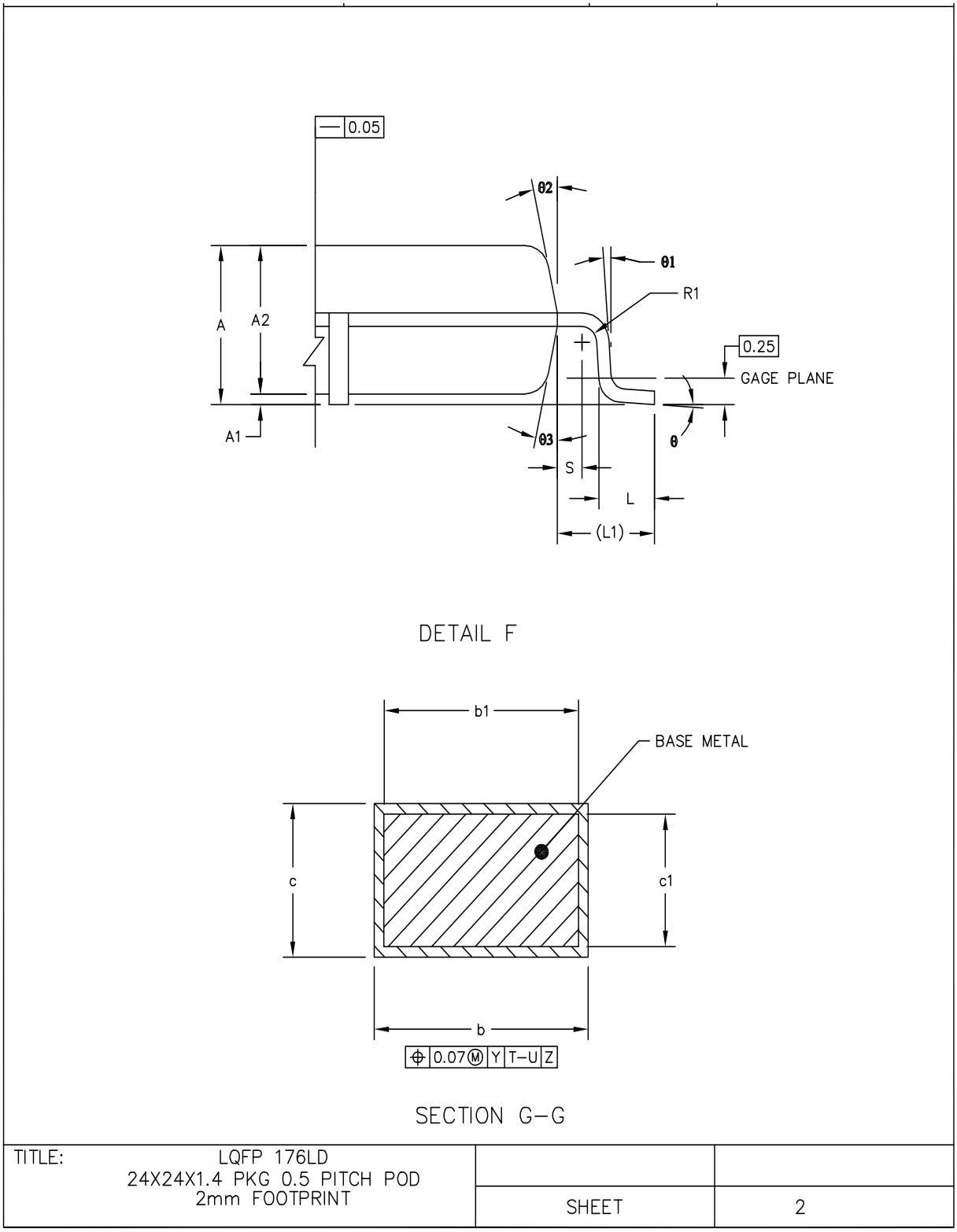
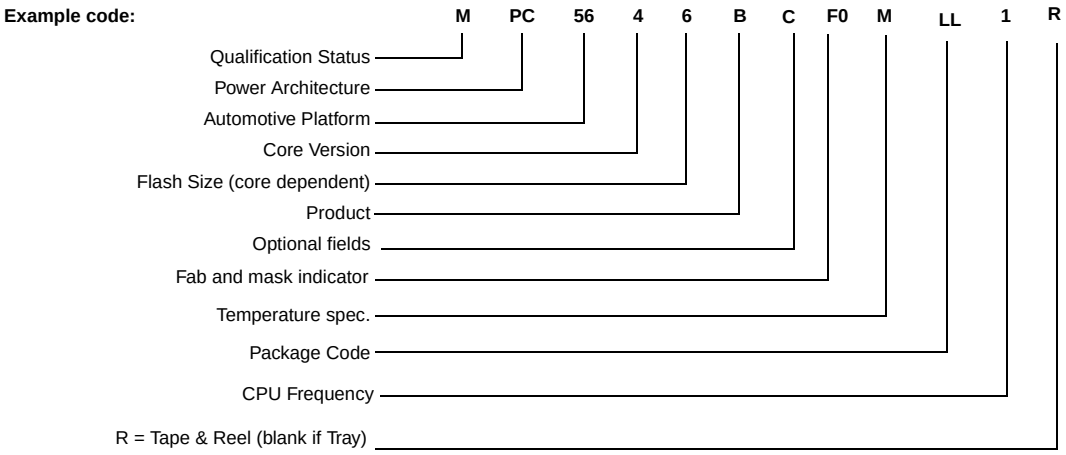


Figure 38. 176 LQFP mechanical drawing (Part 2 of 3)

6 Ordering information



Qualification Status
M = MC status
S = Auto qualified
P = PC status

PC = Power Architecture

Automotive Platform
56 = Power Architecture in 90 nm

Core Version
4 = e200z4d core version (highest core version in the case of multiple cores)

Flash Memory Size
4 = 1.5 MB
5 = 2 MB
6 = 3 MB

Product Version
B = Body
C = Gateway

Optional fields
C = CSE module available
Blank = none of these options available

Fab and mask version indicator
F = ATMC
0 = First version of the mask

Temperature spec.
C = –40 °C to 85 °C
V = –40 °C to 105 °C
M = –40 °C to 125 °C

Package Code
LU = 176 LQFP
LT = 208 LQFP
MJ = 256 MAPBGA

CPU Frequency
1 = e200z4d operates up to 120 MHz
8 = e200z4d operates up to 80 MHz

Shipping Method
R = Tape and reel
Blank = Tray

Note: Not all options are available on all devices. Refer to Table 1, which shows the orderable part numbers for MPC564xx.

Figure 45. Orderable parts